

Detlef Hommel

List of Publications by Year in descending order

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604
papers

10,921
citations

44066

48
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56717

83
g-index

607
all docs

607
docs citations

607
times ranked

6848
citing authors

#	ARTICLE	IF	CITATIONS
1	Superradiance of quantum dots. Nature Physics, 2007, 3, 106-110.	16.7	432
2	Fine Structure of Biexciton Emission in Symmetric and Asymmetric CdSe/ZnSe Single Quantum Dots. Physical Review Letters, 1999, 82, 1780-1783.	7.8	357
3	Microstructure of heteroepitaxial GaN revealed by x-ray diffraction. Journal of Applied Physics, 2003, 93, 8918-8925.	2.5	342
4	X-ray diffraction analysis of the defect structure in epitaxial GaN. Applied Physics Letters, 2000, 77, 2145-2147.	3.3	312
5	Free-carrier and phonon properties of n- and p-type hexagonal GaN films measured by infrared ellipsometry. Physical Review B, 2000, 62, 7365-7377.	3.2	233
6	Direct Observation of Optically Injected Spin-Polarized Currents in Semiconductors. Physical Review Letters, 2003, 90, 216601.	7.8	212
7	Emission properties of a-plane GaN grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2005, 98, 093519.	2.5	189
8	E0 band gap energy and lattice constant of ternary Zn _{1-x} Mg _x Se as functions of composition. Applied Physics Letters, 1996, 69, 97-99.	3.3	188
9	The role of high-temperature island coalescence in the development of stresses in GaN films. Applied Physics Letters, 2001, 78, 1976-1978.	3.3	185
10	Biexciton versus Exciton Lifetime in a Single Semiconductor Quantum Dot. Physical Review Letters, 1999, 83, 4417-4420.	7.8	180
11	Single-photon emission of CdSe quantum dots at temperatures up to 200 K. Applied Physics Letters, 2002, 81, 2920-2922.	3.3	169
12	Composition mapping in InGaN by scanning transmission electron microscopy. Ultramicroscopy, 2011, 111, 1316-1327.	1.9	156
13	In situ and ex situ evaluation of the film coalescence for GaN growth on GaN nucleation layers. Journal of Crystal Growth, 2000, 221, 262-266.	1.5	137
14	Single zero-dimensional excitons in CdSe/ZnSe nanostructures. Applied Physics Letters, 1998, 73, 3105-3107.	3.3	134
15	Excitons, biexcitons, and phonons in ultrathin CdSe/ZnSe quantum structures. Physical Review B, 1999, 60, 8773-8782.	3.2	115
16	Direct observation of free-exciton thermalization in quantum-well structures. Physical Review B, 1998, 57, 1390-1393.	3.2	114
17	Strain relaxation in AlGaIn under tensile plane stress. Journal of Applied Physics, 2000, 88, 7029-7036.	2.5	113
18	Relaxation and mosaicity profiles in epitaxial layers studied by high resolution X-ray diffraction. Journal of Crystal Growth, 1994, 135, 41-52.	1.5	111

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19	Temperature dependence of the thermal expansion of GaN. Physical Review B, 2005, 72, .	3.2	105
20	Spectral diffusion of the exciton transition in a single self-organized quantum dot. Applied Physics Letters, 2000, 76, 1872-1874.	3.3	104
21	Stark effect and polarizability in a single CdSe/ZnSe quantum dot. Applied Physics Letters, 2001, 79, 1033-1035.	3.3	104
22	Anisotropic strain and phonon deformation potentials in GaN. Physical Review B, 2007, 75, .	3.2	99
23	Local vibrational modes in Mg-doped GaN grown by molecular beam epitaxy. Applied Physics Letters, 1999, 74, 3281-3283.	3.3	89
24	Quantum Optical Studies on Individual Acceptor Bound Excitons in a Semiconductor. Physical Review Letters, 2002, 89, 177403.	7.8	88
25	Incorporation of indium during molecular beam epitaxy of InGaN. Applied Physics Letters, 1998, 73, 3232-3234.	3.3	86
26	CdSe/ZnSe quantum structures grown by migration enhanced epitaxy: Structural and optical investigations. Applied Physics Letters, 1997, 71, 1510-1512.	3.3	83
27	Temperature dependence of the thermal expansion of AlN. Applied Physics Letters, 2009, 94, .	3.3	83
28	Binding-energy distribution and dephasing of localized biexcitons. Physical Review B, 1997, 55, R7383-R7386.	3.2	75
29	Stress and wafer bending of a-plane GaN layers on r-plane sapphire substrates. Journal of Applied Physics, 2006, 100, 103511.	2.5	67
30	Strong phase separation of strained In \times Ga \times alloys. Applied Physics Letters, 2006, 89, 103101.	3.2	66
31	Lateral quantization effects in lithographically defined CdZnSe/ZnSe quantum dots and quantum wires. Applied Physics Letters, 1995, 67, 124-126.	3.3	62
32	Density Dependence of the Exciton Energy in Semiconductors. Physical Review Letters, 1998, 80, 4943-4946.	7.8	62
33	Magnesium segregation and the formation of pyramidal defects in p-GaN. Applied Physics Letters, 2002, 81, 4748-4750.	3.3	62
34	Analysis of the Defect Structure of Epitaxial GaN. Physica Status Solidi A, 1999, 176, 391-395.	1.7	59
35	Suburban Transmission of Q Fever in French Guiana: Evidence of a Wild Reservoir. Journal of Infectious Diseases, 2001, 184, 278-284.	4.0	58
36	Room temperature single photon emission from an epitaxially grown quantum dot. Applied Physics Letters, 2012, 100, 061114.	3.3	58

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37	Plasmodium falciparum parasites in French Guiana: limited genetic diversity and high selfing rate.. American Journal of Tropical Medicine and Hygiene, 1999, 61, 978-985.	1.4	58
38	Optical and structural characterization of AlInN layers for optoelectronic applications. Journal of Applied Physics, 2010, 108, .	2.5	57
39	First order distributed feedback operation in ZnSe based laser structures. Applied Physics Letters, 1995, 67, 1-3.	3.3	56
40	CdSe/ZnSe Quantum Dot Structures: Structural and Optical Investigations. Physica Status Solidi (B): Basic Research, 1997, 202, 835-843.	1.5	53
41	Strain relaxation in AlGaIn/GaN superlattices grown on GaN. Journal of Applied Physics, 2001, 89, 2160-2167.	2.5	53
42	Phase diagram and critical behavior of the random ferromagnet $Ga_{1-x}Mn_xN$. Physical Review B, 2013, 88, .	3.2	53
43	Electron-phonon quantum kinetics in the strong-coupling regime. Physical Review B, 1999, 60, 12079-12090.	3.2	52
44	Electrically pumped lasing from CdSe quantum dots. Electronics Letters, 2001, 37, 1119.	1.0	51
45	Quantum dot formation by segregation enhanced CdSe reorganization. Journal of Applied Physics, 2002, 92, 6546-6552.	2.5	51
46	Intensity-dependent energy and line shape variation of donor-acceptor pair bands in ZnSe:N at different compensation levels. Applied Physics Letters, 1995, 67, 1914-1916.	3.3	49
47	Deep europium-bound exciton in a ZnS lattice. Physical Review B, 1990, 42, 3628-3633.	3.2	48
48	Dengue encephalitis in French Guiana. Research in Virology, 1998, 149, 235-238.	0.7	48
49	$Ga_{1-x}Mn_xN$ epitaxial films with high magnetization. Applied Physics Letters, 2012, 101, .	3.3	48
50	Mosaicity of GaN Epitaxial Layers: Simulation and Experiment. Physica Status Solidi (B): Basic Research, 2001, 228, 403-406.	1.5	44
51	560-nm-continuous wave laser emission from ZnSe-based laser diodes on GaAs. Applied Physics Letters, 2001, 79, 2523-2525.	3.3	44
52	Spatiotemporal dynamics of quantum-well excitons. Physical Review B, 2003, 67, .	3.2	43
53	Confined optical modes in monolithic II-VI pillar microcavities. Applied Physics Letters, 2006, 88, 051101.	3.3	43
54	Room temperature emission from $CdSe_{1-x}ZnS_x$ MgS single quantum dots. Applied Physics Letters, 2007, 90, 101114.	3.3	41

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55	Polarization-dependent formation of biexcitons in (Zn,Cd)Se/ZnSe quantum wells. <i>Physical Review B</i> , 1997, 55, 9866-9871.	3.2	39
56	In as a surfactant for the growth of GaN (0001) by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001, 79, 3425-3427.	3.3	39
57	500-560 nm Laser Emission from Quaternary CdZnSse Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 935-942.	1.5	39
58	Single photon emission from InGaN/GaN quantum dots up to 50â€%K. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	39
59	Determination of the Temperature Dependent Thermal Expansion Coefficients of Bulk AlN by HRXRD. <i>Acta Physica Polonica A</i> , 2008, 114, 1193-1200.	0.5	38
60	Formation of self-assembling IIâ€VI semiconductor nanostructures during migration enhanced epitaxy. <i>Journal of Crystal Growth</i> , 1998, 184-185, 259-263.	1.5	37
61	Energy structure and recombination for ZnS bulk crystals doped with Tb, Er and Eu. <i>Journal of Crystal Growth</i> , 1985, 72, 346-350.	1.5	36
62	Impact of defects on the carrier transport in GaN. <i>Journal of Crystal Growth</i> , 1998, 189-190, 763-767.	1.5	36
63	Segregation-enhanced etching of Cd during Zn deposition on CdSe quantum dots. <i>Physical Review B</i> , 2001, 64, .	3.2	36
64	Eu ²⁺ photocharge transfer processes in zns crystals determined by photo-esr measurements. <i>Physica Status Solidi A</i> , 1986, 95, 261-268.	1.7	35
65	Propagation of femtosecond pulses in thin ZnSe layers. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 196, 473-485.	1.5	35
66	Structural defect-related emissions in nonpolar a-plane GaN. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 473-476.	2.7	34
67	Influence of Coulomb correlations on gain and stimulated emission in (Zn,Cd)Se/Zn(S,Se)/(Zn,Mg)(S,Se) quantum-well lasers. <i>Physical Review B</i> , 1998, 58, 2055-2063.	3.2	33
68	New Concept for ZnTe-Based Homoepitaxial Light-Emitting Diodes Grown by Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2002, 192, 177-182.	1.7	33
69	Polarization dynamics in self-assembled CdSe/ZnSe quantum dots:â€fThe role of excess energy. <i>Physical Review B</i> , 2003, 67, .	3.2	33
70	Green monolithic IIâ€VI vertical-cavity surface-emitting laser operating at room temperature. <i>Physica Status Solidi (B): Basic Research</i> , 2004, 241, 731-738.	1.5	32
71	High-reflectivity broadband distributed Bragg reflector lattice matched to ZnTe. <i>Applied Physics Letters</i> , 2009, 94, 191108.	3.3	32
72	Blueâ€Green ZnSe Laser Diodes for Optoelectronics. Present State at WÃ¼rzburg University. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 269-277.	1.5	31

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73	High-density effects, stimulated emission, and electrooptical properties of ZnCdSe/ZnSe single quantum wells and laser diodes. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 194, 199-217.	1.5	31
74	Dynamical properties of excitons in Zn _{1-x} CdxSe/ZnSe quantum wells and Zn _{1-x} CdxSe epilayers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1994, 138, 861-867.	1.5	30
75	Optical properties of Zn _{1-x} MgxSySe _{1-y} epitaxial layers for blue-green laser applications. <i>Journal of Applied Physics</i> , 1995, 77, 5377-5380.	2.5	30
76	Ion-induced crystal damage during plasma-assisted MBE growth of GaN layers. <i>Physical Review B</i> , 1998, 58, 15749-15755.	3.2	30
77	Thermal expansion of bulk and homoepitaxial GaN. <i>Applied Physics Letters</i> , 2000, 77, 1434-1436.	3.3	30
78	Strain in cracked AlGaIn layers. <i>Journal of Applied Physics</i> , 2002, 92, 118-123.	2.5	30
79	InGaIn quantum dot growth in the limits of Stranski-Krastanov and spinodal decomposition. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1765-1776.	1.5	30
80	Inhibition and Enhancement of the Spontaneous Emission of Quantum Dots in Micropillar Cavities with Radial-Distributed Bragg Reflectors. <i>ACS Nano</i> , 2014, 8, 9970-9978.	14.6	30
81	First Case of Yellow Fever in French Guiana since 1902. <i>Emerging Infectious Diseases</i> , 1999, 5, 429-432.	4.3	29
82	Acute Renal Failure Associated with Dengue Fever in French Guiana. <i>Nephron</i> , 1999, 83, 183-183.	1.8	29
83	Single-electron charging of a self-assembled InAs quantum dot. <i>Applied Physics Letters</i> , 2003, 82, 3946-3948.	3.3	29
84	Optical bandpass switching by modulating a microcavity using ultrafast acoustics. <i>Physical Review B</i> , 2010, 81, .	3.2	29
85	Analysis of deep traps in hexagonal molecular beam epitaxy-grown GaN by admittance spectroscopy. <i>Journal of Applied Physics</i> , 1998, 84, 2040-2043.	2.5	28
86	Preconditioning of c-plane sapphire for GaN molecular beam epitaxy by electron cyclotron resonance plasma nitridation. <i>Journal of Applied Physics</i> , 1998, 83, 6023-6027.	2.5	28
87	Multiple African Honeybee Stings and Acute Renal Failure. <i>Nephron</i> , 1998, 78, 235-236.	1.8	27
88	Negatively charged trion in ZnSe single quantum wells with very low electron densities. <i>Physical Review B</i> , 2000, 62, 7413-7419.	3.2	27
89	Micro-photoluminescence studies of InGaIn/GaN quantum dots up to 150 K. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1661-1664.	1.5	27
90	Observation of a hybrid state of Tamm plasmons and microcavity exciton polaritons. <i>Scientific Reports</i> , 2016, 6, 34392.	3.3	27

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91	Bandgap engineering in III-nitrides with boron and group V elements: Toward applications in ultraviolet emitters. Applied Physics Reviews, 2020, 7, .	11.3	27
92	Optically detected cyclotron resonance properties of high purity ZnSe epitaxial layers grown on GaAs. Applied Physics Letters, 1997, 71, 1116-1117.	3.3	26
93	Highly ordered catalyst-free and mask-free GaN nanorods on-plane sapphire. Nanotechnology, 2009, 20, 075604.	2.6	26
94	Band gap bowing of binary alloys: Experimental results compared to theoretical tight-binding supercell calculations for $\langle \text{Cd} \rangle$. Physical Review B, 2010, 82, .	3.2	26
95	Fabrication of CdZnSe/ZnSe quantum dots and quantum wires by electron beam lithography and wet chemical etching. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2792.	1.6	25
96	Laterally structured ZnCdSe/ZnSe superlattices by diffusion induced disordering. Applied Physics Letters, 1996, 69, 2647-2649.	3.3	25
97	Raman scattering from defects in GaN: The question of vibrational or electronic scattering mechanism. Physical Review B, 1998, 58, 13619-13626.	3.2	25
98	Size dependence of strain relaxation and lateral quantization in deep etched $\text{Cd}_{x}\text{Zn}_{1-x}\text{Se}/\text{ZnSe}$ quantum wires. Physical Review B, 1998, 57, 15439-15447.	3.2	25
99	Near-field photoluminescence imaging of single defects in a ZnSe quantum-well structure at low temperatures. Applied Physics Letters, 2000, 76, 203-205.	3.3	25
100	Polariton propagation in shallow-confinement heterostructures: Microscopic theory and experiment showing the breakdown of the dead-layer concept. Physical Review B, 2004, 70, .	3.2	25
101	Electroluminescence from a single InGaN quantum dot in the green spectral region up to 150 K. Nanotechnology, 2010, 21, 015204.	2.6	25
102	Exciton-Polariton Gas as a Nonequilibrium Coolant. Physical Review Letters, 2015, 114, 186403.	7.8	25
103	Nature of the charge transfer states of the trigonal and tetragonal Eu^{3+} centers in CdF_2 crystals. Journal of Luminescence, 1979, 18-19, 281-284.	3.1	24
104	p-type Doping of ZnSe. On the Properties of Nitrogen in ZnSe:N. Physica Status Solidi (B): Basic Research, 1995, 187, 393-399.	1.5	24
105	Electro-Optical Characterization of CdSe Quantum Dot Laser Diodes. Physica Status Solidi (B): Basic Research, 2002, 229, 1029-1032.	1.5	24
106	XPS studies on the role of arsenic incorporated into GaN. Vacuum, 2019, 167, 73-76.	3.5	24
107	Two-dimensional Shubnikov-de Haas oscillations in modulation-doped CdTe/CdMnTe quantum well structures. Applied Physics Letters, 1993, 62, 3010-3012.	3.3	23
108	The growth start on the heterovalent GaAs-ZnSe interface under Te, Se and Zn termination. Journal of Crystal Growth, 1996, 159, 761-765.	1.5	23

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109	Molecular beam epitaxial growth and characterization of ZnSe on (001) ZnSe substrates and its application in light-emitting diodes. <i>Semiconductor Science and Technology</i> , 1996, 11, 107-115.	2.0	23
110	Doping dependent ZnCdSe/ZnSe-superlattice disordering. <i>Applied Physics Letters</i> , 1997, 71, 243-245.	3.3	23
111	Exciton localisation in CdSe islands buried in a quantum well of Zn _{1-x} Cd _x Se. <i>Journal of Crystal Growth</i> , 1998, 184-185, 306-310.	1.5	23
112	Compensation mechanisms in ZnSe:N and codoped ZnSe:N:Cl. <i>Physical Review B</i> , 1998, 57, 12869-12873.	3.2	23
113	Compensation mechanism in MOCVD and MBE grown GaN:Mg. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 38-41.	2.7	23
114	Green laser emission from monolithic II-VI-based pillar microcavities near room temperature. <i>Applied Physics Letters</i> , 2008, 92, 031101.	3.3	23
115	Strong coupling in monolithic microcavities with ZnSe quantum wells. <i>Applied Physics Letters</i> , 2012, 100, 161104.	3.3	23
116	Micropillar Cavity Containing a CdTe Quantum Dot with a Single Manganese Ion. <i>Crystal Growth and Design</i> , 2014, 14, 988-992.	3.0	23
117	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. <i>Scientific Reports</i> , 2017, 7, 41877.	3.3	23
118	Radiative recombination centers induced by stacking-fault pairs in ZnSe/ZnMgSSe quantum-well structures. <i>Applied Physics Letters</i> , 1999, 75, 3944-3946.	3.3	22
119	Spatially modified layer properties related to the formation of gallium droplets on GaN(0001) surfaces during plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001, 78, 3827-3829.	3.3	22
120	Stress analysis of Al _x Ga _{1-x} N films with microcracks. <i>Applied Physics Letters</i> , 2003, 82, 367-369.	3.3	22
121	Enhanced spontaneous emission of CdSe quantum dots in monolithic II-VI pillar microcavities. <i>Applied Physics Letters</i> , 2006, 89, 091107.	3.3	22
122	Optical Study of ZnS:Mn Thin Films with High Mn Concentrations. <i>Physica Status Solidi A</i> , 1984, 81, 695-700.	1.7	21
123	Chlorine: A new efficient δ -type dopant in CdTe layers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992, 61, 1546-1548.	3.3	21
124	Measurements of the absolute external luminescence quantum efficiency in ZnSe/ZnMgSSe multiple quantum wells as a function of temperature. <i>Journal of Applied Physics</i> , 1998, 84, 6871-6876.	2.5	21
125	Device Properties of Homo- and Heteroepitaxial ZnSe-Based Laser Diodes. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2590-2597.	1.5	21
126	Realization of a GaN Laser Diode with Wet Etched Facets. <i>Physica Status Solidi A</i> , 2002, 191, R3-R5.	1.7	21

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127	Heat generation and dissipation in GaN-based light emitting devices. <i>Physica Status Solidi A</i> , 2003, 200, 83-86.	1.7	21
128	Pronounced Purcell enhancement of spontaneous emission in CdTe/ZnTe quantum dots embedded in micropillar cavities. <i>Applied Physics Letters</i> , 2012, 101, 132105.	3.3	21
129	Optical study of interdiffusion in CdTe and ZnSe based quantum wells. <i>Journal of Crystal Growth</i> , 1994, 138, 362-366.	1.5	20
130	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. <i>Journal of Electronic Materials</i> , 2004, 33, 389-394.	2.2	20
131	Resonant modes in monolithic nitride pillar microcavities. <i>European Physical Journal B</i> , 2005, 48, 291-294.	1.5	20
132	Spatially resolved distribution of dislocations and crystallographic tilts in GaN layers grown on Si(111) substrates by maskless cantilever epitaxy. <i>Journal of Applied Physics</i> , 2006, 100, 053103.	2.5	20
133	The dominant shallow 0.225 eV acceptor in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1604-1608.	1.5	20
134	Electrically driven single quantum dot emitter operating at room temperature. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	20
135	Growth and characterization of nitride-based distributed Bragg reflectors. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1748-1755.	1.5	20
136	Determination of dislocation density in GaN/sapphire layers using XRD measurements carried out from the edge of the sample. <i>Journal of Alloys and Compounds</i> , 2020, 825, 153838.	5.5	20
137	Direct observation of localized impurity excited states degenerate with conduction band (CdF ₂ : Eu). <i>Journal of Luminescence</i> , 1981, 24-25, 217-220.	3.1	19
138	Molecular beam epitaxial growth mechanism of ZnSe epilayers on (100) GaAs as determined by reflection high-energy electron diffraction, transmission electron microscopy and X-ray diffraction. <i>Journal of Crystal Growth</i> , 1994, 138, 48-54.	1.5	19
139	Intensity-dependent energy and lineshape variation of donor-acceptor-pair bands in highly compensated ZnSe:N. <i>Journal of Crystal Growth</i> , 1996, 159, 252-256.	1.5	19
140	Plasma assisted molecular beam epitaxy growth of GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997, 50, 12-15.	3.5	19
141	Thermalization of free excitons in ZnSe quantum wells. <i>Journal of Crystal Growth</i> , 1998, 184-185, 795-800.	1.5	19
142	Thermally induced stress in GaN layers with regard to film coalescence. <i>Journal of Crystal Growth</i> , 2001, 230, 357-360.	1.5	19
143	X-ray scattering from GaN epitaxial layers - an example of highly anisotropic coherence. <i>Journal Physics D: Applied Physics</i> , 2001, 34, A25-A29.	2.8	19
144	Fine tuning of quantum-dot pillar microcavities by focused ion beam milling. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	19

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145	Q Fever in French Guiana: New Trends. <i>Emerging Infectious Diseases</i> , 1998, 4, 131-132.	4.3	19
146	Recombination processes in ZnS:Sm. <i>Physical Review B</i> , 1991, 43, 9955-9958.	3.2	18
147	Bleaching of excitons in a (Zn,Cd)Se/Zn(S,Se)/(Zn,Mg)(S,Se) laser diode under lasing conditions. <i>Physical Review B</i> , 1995, 52, 4736-4739.	3.2	18
148	High-resolution x-ray diffraction investigations of highly mismatched II-VI quantum wells. <i>Journal Physics D: Applied Physics</i> , 1999, 32, A42-A46.	2.8	18
149	Growth of self-assembled (Zn)CdSe nanostructures on ZnSe by migration enhanced epitaxy. <i>Journal of Crystal Growth</i> , 1999, 201-202, 1222-1225.	1.5	18
150	Internal photoluminescence in ZnSe homoepitaxy and application in blue-green-orange mixed-color light-emitting diodes. <i>Journal of Crystal Growth</i> , 2000, 214-215, 1075-1079.	1.5	18
151	Manipulating single quantum dot states in a lateral electric field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 147-150.	2.7	18
152	Bound polarons in semiconductor nanostructures. <i>Physical Review B</i> , 2003, 67, .	3.2	18
153	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. <i>Journal of Alloys and Compounds</i> , 2018, 747, 946-959.	5.5	18
154	Thermoluminescence and photochromism of CdF ₂ : Eu. <i>Physica Status Solidi A</i> , 1975, 31, K81-K84.	1.7	17
155	Bromine doping of CdTe and CdMnTe epitaxial layers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1993, 129, 243-248.	1.5	17
156	The growth of HgSe by molecular beam epitaxy for ohmic contacts to p-ZnSe. <i>Journal of Crystal Growth</i> , 1994, 138, 471-476.	1.5	17
157	Exciton Dynamics and Gain Mechanisms in Optically Pumped ZnSe-Based Laser Structures. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 423-434.	1.5	17
158	Biexciton formation in CdxZn1-xSe/ZnSe quantum-dot and quantum-well structures. <i>Physical Review B</i> , 1997, 56, 15261-15263.	3.2	17
159	Biexcitonic gain characteristics in ZnSe-based lasers with binary wells. <i>Physical Review B</i> , 1999, 60, 5743-5750.	3.2	17
160	Compositional inhomogeneities in InGaN studied by transmission electron microscopy and spatially resolved cathodoluminescence. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999, 59, 279-282.	3.5	17
161	Nondestructive detection of stacking faults for optimization of CdSe/ZnSe quantum-dot structures. <i>Applied Physics Letters</i> , 2000, 77, 3544-3546.	3.3	17
162	Optical Gain of CdSe Quantum Dot Stacks. <i>Physica Status Solidi A</i> , 2002, 190, 593-597.	1.7	17

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163	ZnSe-based laser diodes: New approaches. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1098-1105.	0.8	17
164	First order gain and index coupled distributed feedback lasers in ZnSe-based structures with finely tunable emission wavelengths. <i>Applied Physics Letters</i> , 1996, 68, 599-601.	3.3	16
165	Spin-flip Raman scattering of wide-band-gap II-VI ternary alloys. <i>Physical Review B</i> , 1999, 60, 13555-13560.	3.2	16
166	Association of Tonate Virus (Subtype IIIB of the Venezuelan Equine Encephalitis Complex) with Encephalitis in a Human. <i>Clinical Infectious Diseases</i> , 2000, 30, 188-190.	5.8	16
167	Optical and Structural Properties of CdSe/Zn(S)Se Quantum Dot Stacks. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 143-146.	1.5	16
168	Improved capping layer growth towards increased stability of InGaN quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S561-S564.	0.8	16
169	Rare earths in II-VI compounds: Non-linear optical excitation processes at low and high doping levels. <i>Journal of Crystal Growth</i> , 1990, 101, 393-403.	1.5	15
170	Molecular beam epitaxy grown ZnSe studied by reflectance anisotropy spectroscopy and reflection high-energy electron diffraction. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 2757.	1.6	15
171	ZnSe-Based Laser Diodes and LEDs Grown on ZnSe and GaAs Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 202, 683-693.	1.5	15
172	Polytypism in epitaxially grown gallium nitride. <i>Journal of Crystal Growth</i> , 2000, 208, 57-64.	1.5	15
173	Tunneling of zero-dimensional excitons in a single pair of correlated quantum dots. <i>Physical Review B</i> , 2001, 64, .	3.2	15
174	Post-growth p-type doping enhancement for ZnSe-based lasers using a Li ₃ N interlayer. <i>Applied Physics Letters</i> , 2002, 81, 4916-4918.	3.3	15
175	Luminescence of epitaxial sub-monolayer CdSe nanostructures in ZnSe. <i>Journal of Luminescence</i> , 2005, 112, 177-180.	3.1	15
176	Interfacial structure of a-plane GaN grown on r-plane sapphire. <i>Applied Physics Letters</i> , 2007, 90, 081918.	3.3	15
177	Growth of AlN by pulsed and conventional MOVPE. <i>Journal of Crystal Growth</i> , 2013, 381, 100-106.	1.5	15
178	Polariton lasing in high-quality selenide-based micropillars in the strong coupling regime. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	15
179	Halogen doping of II-VI semiconductors during molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1994, 138, 437-442.	1.5	14
180	Deep Etched ZnSe-Based Nanostructures for Future Optoelectronic Applications. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 371-377.	1.5	14

#	ARTICLE	IF	CITATIONS
181	(Cd,Zn)Se multi-quantum-well LEDs: homoepitaxy on ZnSe substrates and heteroepitaxy on buffer layers. <i>Journal of Crystal Growth</i> , 1996, 159, 26-31.	1.5	14
182	Buffer layers for the growth of GaN on sapphire by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1999, 201-202, 433-436.	1.5	14
183	High Reflectivity p-Type Doped Distributed Bragg Reflectors Using ZnSe/MgS Superlattices. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 111-115.	1.5	14
184	Correlated stacks of CdSe/ZnSSe quantum dots. <i>Applied Physics Letters</i> , 2004, 84, 4367-4369.	3.3	14
185	Carrier-induced changes of the phase of reflected light at a pumped ZnSe layer. <i>Physical Review B</i> , 2005, 72, .	3.2	14
186	A novel approach for the growth of InGaN quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 3955-3958.	0.8	14
187	Atomic structure of the non-polar GaN(0001) surface by cross-sectional scanning tunneling microscopy. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009, 3, 91-93.	2.4	14
188	Growth mechanisms of CdTe during molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1992, 72, 3492-3496.	2.5	13
189	Coherent dynamics of excitons and excitonic complexes in ZnSe epilayers. <i>Journal of the Optical Society of America B: Optical Physics</i> , 1996, 13, 1256.	2.1	13
190	Lateral motion of confined excitonic polaritons. <i>Physical Review B</i> , 1998, 57, 9208-9213.	3.2	13
191	Influence of buffer layers on the structural properties of molecular beam epitaxy grown GaN layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999, 59, 47-51.	3.5	13
192	Analysis of Time-Resolved Donor-Acceptor-Pair Recombination in MBE and MOVPE Grown GaN : Mg. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 228, 379-383.	1.5	13
193	Electronic band structure of gallium nitride: a comparative angle-resolved photoemission study of single crystals and thin films. <i>Surface Science</i> , 2002, 507-510, 223-228.	1.9	13
194	The role of the growth temperature for the SiN interlayer deposition in GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2039-2042.	0.8	13
195	Coherent propagation of polaritons in semiconductor heterostructures: Nonlinear pulse transmission in theory and experiment. <i>Physical Review B</i> , 2005, 72, .	3.2	13
196	Investigation of CdSe quantum dots in MgS barriers as active region in light emitting diodes. <i>Journal of Crystal Growth</i> , 2007, 301-302, 789-792.	1.5	13
197	Nonpolar- and m-plane bulk GaN sliced from boules: structural and optical characteristics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2536-2539.	0.8	13
198	Cleaning and growth morphology of GaN and InGaN surfaces. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1800-1809.	1.5	13

#	ARTICLE	IF	CITATIONS
199	Complementary information on CdSe/ZnSe quantum dot local structure from extended X-ray absorption fine structure and diffraction anomalous fine structure measurements. <i>Journal of Alloys and Compounds</i> , 2012, 523, 155-160.	5.5	13
200	Composition and temperature dependence of the refractive index in Cd _{1-x} Mg _x Te epitaxial films. <i>Semiconductor Science and Technology</i> , 1994, 9, 1567-1569.	2.0	12
201	Radiative and nonradiative rates and deep levels in zinc selenide grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1995, 78, 1731-1736.	2.5	12
202	Acceptor bound biexcitons in ZnSe and CdS. <i>Journal of Crystal Growth</i> , 1996, 159, 776-779.	1.5	12
203	Novel results on compensation processes in ZnSe:N. <i>Journal of Crystal Growth</i> , 1996, 159, 289-292.	1.5	12
204	Thermal stability of (Zn,Cd)(Se,S) heterostructures grown on GaAs. <i>Journal of Applied Physics</i> , 1996, 79, 4368.	2.5	12
205	Influence of composition and well-width fluctuations on optical gain in (In, Ga)N multiple quantum wells. <i>Semiconductor Science and Technology</i> , 2001, 16, 406-412.	2.0	12
206	Motion-enhanced magnetic moments of excitons in ZnSe. <i>Physical Review B</i> , 2010, 81, .	3.2	12
207	Monolithic ZnTe-based pillar microcavities containing CdTe quantum dots. <i>Nanotechnology</i> , 2011, 22, 285204.	2.6	12
208	Studies of blue-green laser structures with asymmetric and pseudomorphic ZnSe wave guides. <i>Journal of Crystal Growth</i> , 1994, 138, 1076.	1.5	11
209	Electrical Contacts to p-ZnSe Based on HgSe and ZnTe. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 439-450.	1.5	11
210	Comparative study of molecular beam and migration-enhanced epitaxy of ZnCdSe quantum wells: influence on interface and composition fluctuations. <i>Journal of Crystal Growth</i> , 2000, 214-215, 602-605.	1.5	11
211	Photoelectric properties of the 0.44 eV deep level-to-band transition in gallium nitride investigated by optical admittance spectroscopy. <i>Applied Physics Letters</i> , 2000, 77, 546-548.	3.3	11
212	Polarization dependent X-ray absorption studies of the chemical bonds anisotropy in wurtzite GaN grown at different conditions. <i>Journal of Alloys and Compounds</i> , 2001, 328, 77-83.	5.5	11
213	Interplay of the Triplet Singlet and Triplet State Transitions in Magneto-optical and Time-Resolved Investigation of ZnSe/Zn(S,Se) Single Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 653-657.	1.5	11
214	Diffusion length of carriers and excitons in GaN— influence of epilayer microstructure. <i>Applied Surface Science</i> , 2004, 223, 294-302.	6.1	11
215	Oxide removal from GaN(0001) surfaces. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S305.	0.8	11
216	Excitons in motion in II-VI semiconductors. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1521-1527.	1.5	11

#	ARTICLE	IF	CITATIONS
217	Mg-related acceptors in GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1850-1852.	0.8	11
218	Nitride based heterostructures with Ga- and N-polarity for sensing applications. <i>Journal of Crystal Growth</i> , 2013, 370, 68-73.	1.5	11
219	Surface oxidation of GaN(0001): Nitrogen plasma-assisted cleaning for ultrahigh vacuum applications. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, 051401.	2.1	11
220	Influence of Static Atomic Displacements on Composition Quantification of AlGaIn/GaN Heterostructures from HAADF-STEM Images. <i>Microscopy and Microanalysis</i> , 2014, 20, 1463-1470.	0.4	11
221	The electronic structure of homogeneous ferromagnetic (Ga, Mn)N epitaxial films. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	11
222	Surface studies of physicochemical properties of As films on GaN(0001). <i>Applied Surface Science</i> , 2019, 493, 384-388.	6.1	11
223	On the Incorporation of Rare Earth Ions into II-VI Compounds: ZnS:Eu. <i>Physica Status Solidi A</i> , 1989, 114, 127-133.	1.7	10
224	Structural characterization and interfacial studies of ZnSe based heterostructures on GaAs. <i>Journal of Crystal Growth</i> , 1994, 143, 162-171.	1.5	10
225	Heavy-hole-light-hole quantum beats in nonlinear transmission spectroscopy. <i>Physical Review B</i> , 1996, 53, 10973-10977.	3.2	10
226	Determination of deformation potentials in ZnSe/GaAs strained-layer heterostructures. <i>Physical Review B</i> , 1996, 54, 2028-2034.	3.2	10
227	Influence of strain conditions on exciton dynamics and on thermal stability of photoluminescence of ZnCdSe/ZnSe quantum wells. <i>Applied Physics Letters</i> , 1996, 69, 2843-2845.	3.3	10
228	Relaxation of hot excitons in inhomogeneously broadened Cd _x Zn _{1-x} Se/ZnSe nanostructures. <i>Physical Review B</i> , 1997, 56, 6868-6870.	3.2	10
229	Internal photoluminescence and lifetime of light-emitting diodes on conductive ZnSe substrates. <i>Journal of Applied Physics</i> , 1997, 82, 4690-4692.	2.5	10
230	Excitonic transitions in MBE grown h-GaN with cubic inclusions. <i>Journal of Crystal Growth</i> , 1998, 189-190, 682-686.	1.5	10
231	Calculation of the Coulomb broadening of donor-acceptor pair emission in compensated semiconductors. <i>Physical Review B</i> , 2000, 62, 8023-8029.	3.2	10
232	Probing the electron-LO-phonon interaction of a single impurity state in a semiconductor. <i>Physical Review B</i> , 2001, 63, .	3.2	10
233	Optical Spectroscopy on Non-Magnetic and Semimagnetic Single Quantum Dots in External Fields. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 415-422.	1.5	10
234	Influence of Capping Conditions on CdSe/ZnSe Quantum Dot Formation. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 497-501.	1.5	10

#	ARTICLE	IF	CITATIONS
235	Strain compensated AlGaIn/GaN-Bragg-reflectors with high Al content grown by MOVPE. Journal of Crystal Growth, 2008, 310, 4923-4926.	1.5	10
236	Optical Properties of CdTe QDs Formed Using Zn Induced Reorganization. Acta Physica Polonica A, 2011, 119, 627-629.	0.5	10
237	Efficient n-type doping of CdTe epitaxial layers grown by photo-assisted molecular beam epitaxy with the use of chlorine. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 16, 178-181.	3.5	9
238	Room temperature emission in narrow (14 nm) quantum wires with strong lateral confinement effects. Journal of Crystal Growth, 1996, 159, 455-458.	1.5	9
239	Raman spectroscopy and selective pair luminescence on ZnSe:N. Journal of Crystal Growth, 1996, 159, 276-279.	1.5	9
240	Strain-dependent Zeeman effect of the nitrogen acceptor bound exciton in ZnSe-epilayers. Journal of Crystal Growth, 1996, 159, 302-306.	1.5	9
241	On the growth and doping of blue-green emitting ZnSe laser diodes. Journal of Crystal Growth, 1996, 159, 566-572.	1.5	9
242	Characterization of electronic states in molecular beam epitaxy grown GaN by optical admittance spectroscopy: Comparison of different nitrogen plasma sources. Applied Physics Letters, 1999, 74, 2032-2034.	3.3	9
243	Phonon interaction of single excitons in CdSe/ZnSe quantum dot structures. Journal of Luminescence, 1999, 83-84, 305-308.	3.1	9
244	Optical Spectroscopy on One and Two Exciton States in ZnSe-Based Single Quantum Dots. Physica Status Solidi A, 2000, 178, 323-326.	1.7	9
245	Evidence for Phase Separation in InGaIn by Resonant Raman Scattering. Physica Status Solidi A, 2000, 179, R4-R6.	1.7	9
246	Direct evidence for the trigonal symmetry of shallow phosphorus acceptors in ZnSe. Physical Review B, 2001, 64, .	3.2	9
247	Excitation Spectroscopy on Single Quantum Dots and Single Pairs of Quantum Dots. Physica Status Solidi (B): Basic Research, 2002, 229, 503-507.	1.5	9
248	Energy renormalization and binding energy of the biexciton. Physical Review B, 2003, 67, .	3.2	9
249	Optoelectronic devices on bulk GaN. Journal of Crystal Growth, 2005, 281, 101-106.	1.5	9
250	Ordering mechanism of stacked CdSe/ZnS quantum dots: A combined reciprocal-space and real-space approach. Physical Review B, 2005, 72, .	3.2	9
251	TEM analyses of wurtzite InGaIn islands grown by MOVPE and MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1679-1682.	0.8	9
252	Effect of sapphire-substrate thickness on the curvature of thick GaN films grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2007, 102, 123507.	2.5	9

#	ARTICLE	IF	CITATIONS
253	Optical properties of InGaN quantum dots in monolithic pillar microcavities. Applied Physics Letters, 2010, 96, 251906.	3.3	9
254	Light-emitting diode based on mask- and catalyst-free grown N-polar GaN nanorods. Nanotechnology, 2011, 22, 265202.	2.6	9
255	Cleaning of GaN(2Å ⁻¹ 110) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	9
256	Trap levels in the atomic layer deposition-ZnO/GaN heterojunctionâ€™Thermal admittance spectroscopy studies. Journal of Applied Physics, 2013, 113, .	2.5	9
257	Light-matter coupling in ZnTe-based micropillar cavities containing CdTe quantum dots. Journal of Applied Physics, 2013, 113, 136504.	2.5	9
258	Lonomia caterpillar envenoming in French Guiana reversed by the Brazilian antivenom: A successful case of international cooperation for a rare but deadly tropical hazard. Toxicon, 2018, 151, 74-78.	1.6	9
259	Boron influence on bandgap and photoluminescence in B GaN grown on AlN. Journal of Applied Physics, 2020, 127, .	2.5	9
260	RHEED studies of MBE growth mechanisms of CdTe and CdMnTe. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 16, 103-107.	3.5	8
261	Angular dependence of resonant Raman and Rayleigh scattering in epitaxial ZnSe layers. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1994, 70, 443-452.	0.6	8
262	Interplay between localized and free exciton recombination in multi quantum well structures. Journal of Crystal Growth, 1996, 159, 533-536.	1.5	8
263	Excitonic lifetimes in (Zn,Cd)Se/ZnSe and ZnSe/Zn(Se,S) quantum wires. Physical Review B, 1996, 53, R4233-R4236.	3.2	8
264	Fabrication of dry etched CdZnSe/ZnSe quantum wires by thermally assisted electron cyclotron resonance etching. Applied Physics Letters, 1997, 71, 344-346.	3.3	8
265	Planar homoepitaxial laser diodes grown on aluminium-doped ZnSe substrates. Electronics Letters, 1998, 34, 891.	1.0	8
266	Growth and characterization of IIâ€™VI semiconductor lasers. FestkÃ¶rperprobleme, 1999, , 47-60.	0.7	8
267	Relation between spin and momentum relaxation in ZnSe/ZnMgSSe quantum wells. Physica B: Condensed Matter, 1999, 272, 338-340.	2.7	8
268	Correlations between Structural, Electrical and Optical Properties of GaN Layers Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 1999, 216, 659-662.	1.5	8
269	Studies on Carbon as Alternative P-Type Dopant for Gallium Nitride. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 526-531.	1.0	8
270	High temperature AlN intermediate layer in GaN grown by molecular beam epitaxy. Journal of Crystal Growth, 2000, 216, 15-20.	1.5	8

#	ARTICLE	IF	CITATIONS
271	Exciton-phonon interaction in epitaxial CdSe/ZnSe nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 238, 317-320.	1.5	8
272	GaN based laser diodes - epitaxial growth and device fabrication. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1846-1859.	0.8	8
273	Crystallographic wing tilt in laterally overgrown GaN. <i>Journal Physics D: Applied Physics</i> , 2003, 36, A188-A191.	2.8	8
274	White X-ray microbeam analysis of strain and crystallographic tilt in GaN layers grown by maskless pendeoepitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 732-738.	1.8	8
275	On the microstructure of Al _x Ga _{1-x} N layers grown on 6H-SiC(0001) substrates. <i>Journal of Applied Physics</i> , 2005, 97, 083501.	2.5	8
276	Photoluminescence of a-plane GaN: comparison between MOCVD and HVPE grown layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1499-1502.	0.8	8
277	Optical characterization of In _x Ga _{1-x} N alloys. <i>Applied Surface Science</i> , 2006, 253, 254-257.	6.1	8
278	Defect structure of a-plane GaN grown by hydride and metal-organic vapor phase epitaxy on r-plane sapphire. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2564-2567.	0.8	8
279	Direct MOVPE- and MBE-growth of a-plane GaN on r-plane sapphire. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1836-1838.	0.8	8
280	Integration of InGaN quantum dots into nitride-based microcavities. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 2320-2322.	0.8	8
281	TEM characterization of catalyst- and mask-free grown GaN nanorods. <i>Journal of Physics: Conference Series</i> , 2010, 209, 012020.	0.4	8
282	Optical polariton properties in ZnSe-based planar and pillar structured microcavities. <i>European Physical Journal B</i> , 2011, 84, 381-384.	1.5	8
283	Mg and Si dopant incorporation and segregation in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1810-1821.	1.5	8
284	Tailoring the optical properties of wide-bandgap based microcavities via metal films. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	8
285	Comparison of magneto-optical properties of various excitonic complexes in CdTe and CdSe self-assembled quantum dots. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 265302.	1.8	8
286	Polarization-dependent XAFS and density functional theory investigations of the quality of the epitaxial GaMnN structure. <i>Journal of Alloys and Compounds</i> , 2017, 725, 632-638.	5.5	8
287	As-related stability of the band gap temperature dependence in N-rich GaNAs. <i>Applied Physics Letters</i> , 2019, 115, 092106.	3.3	8
288	Improved-sensitivity integral SQUID magnetometry of (Ga,Mn)N thin films in proximity to Mg-doped GaN. <i>Journal of Alloys and Compounds</i> , 2021, 868, 159119.	5.5	8

#	ARTICLE	IF	CITATIONS
289	Epitaxial ZnO Films Grown at Low Temperature for Novel Electronic Application. Acta Physica Polonica A, 2011, 120, A-7-A-10.	0.5	8
290	Anisotropic thermal conductivity of AlGaIn/GaN superlattices. Nanotechnology, 2021, 32, 075707.	2.6	8
291	Novel excitation mechanism of rare earth intra-shell emission. Journal of Luminescence, 1988, 40-41, 625-626.	3.1	7
292	The influence of nitrogen on the p-conductivity in ZnSe epilayers grown by molecular beam epitaxy. Journal of Crystal Growth, 1994, 138, 1073-1074.	1.5	7
293	Resonance Brillouin scattering from quantized exciton-polaritons in ultrathin epitaxial layers of ZnSe. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, 1995, 17, 1753-1757.	0.4	7
294	Dynamics of Gain and Stimulated Emission in II-VI Laser Diodes. Physica Status Solidi (B): Basic Research, 1998, 206, 399-406.	1.5	7
295	Quantum confined Stark effect of II-VI heterostructures suitable as modulators in the blue-green spectral region. Applied Physics Letters, 1998, 72, 3320-3322.	3.3	7
296	Analysis of cadmium diffusion in ZnSe by X-ray diffraction and transmission electron microscopy. Journal of Crystal Growth, 2000, 214-215, 585-589.	1.5	7
297	Line shape of four-wave-mixing signals: dependence on sample geometry and excitation conditions. Journal of Crystal Growth, 2000, 214-215, 856-861.	1.5	7
298	On the Way to the II-VI Quantum Dot VCSEL. , 2002, , 13-26.		7
299	Operation and Catastrophic Optical Degradation of II-VI Laser Diodes at Output Powers larger than 1 W. Physica Status Solidi (B): Basic Research, 2002, 229, 943-948.	1.5	7
300	Determination of the Structural and Luminescence Properties of Nitrides Using Electron Backscattered Diffraction and Photo- and Cathodoluminescence. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 532-536.	0.8	7
301	Growth and characterization of self-assembled CdSe quantum dots in MgS barriers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 767-770.	0.8	7
302	Relaxation in crack-free AlN/GaN superlattices. Physica Status Solidi (B): Basic Research, 2006, 243, 1533-1536.	1.5	7
303	In situ observation of Zn-induced etching during CdSe quantum dot formation using time-resolved ellipsometry. Applied Physics Letters, 2007, 90, 221102.	3.3	7
304	Structural investigation of growth and dissolution of nano-islands grown by molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 748-756.	1.5	7
305	A CdSe quantum dot based resonant cavity light-emitting diode showing single line emission up to 90 K. Nanotechnology, 2009, 20, 015401.	2.6	7
306	Electric field-induced exciton localization in quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 551-555.	0.8	7

#	ARTICLE	IF	CITATIONS
307	Far field emission of micropillar and planar microcavities lattice-matched to ZnTe. Open Physics, 2011, 9, 428-431.	1.7	7
308	Electrically driven single photon emission from a CdSe/ZnSSe/MgS semiconductor quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1256-1259.	0.8	7
309	Electrically driven single photon emission from a CdSe/ZnSSe single quantum dot at 200%K. Applied Physics Letters, 2014, 105, .	3.3	7
310	Asymmetric skew X-ray diffraction at fixed incidence angle: application to semiconductor nano-objects. Journal of Applied Crystallography, 2016, 49, 961-967.	4.5	7
311	Arsenicâ€induced Growth of Dodecagonal GaN Microrods with Stable <i>a</i>â€Plane Walls. Advanced Optical Materials, 2021, 9, 2001348.</i>	7.3	7
312	Optical Study of ZnTe-Based 2D and 0D Photonic Structures Containing CdTe/ZnTe Quantum Dots. Acta Physica Polonica A, 2009, 116, 888-889.	0.5	7
313	Emission Patterns of Tb Doped ZnS Bulk Crystals. Physica Status Solidi A, 1984, 81, K199-K203.	1.7	6
314	Discrimination of Sm centers in ZnS by site selective laser spectroscopy. Journal of Luminescence, 1988, 40-41, 391-392.	3.1	6
315	IIâ€VI compounds codoped with transition metals and rare earths. Journal of Luminescence, 1991, 48-49, 655-660.	3.1	6
316	Blue-Green Ternary and Quaternary Lasers. Technological Problems and Theoretical Investigations. Physica Status Solidi (B): Basic Research, 1995, 187, 415-422.	1.5	6
317	Raman scattering by wavevector-dependent LO phonon-plasmon modes in heavily doped n-type ZnSe. Semiconductor Science and Technology, 1995, 10, 785-790.	2.0	6
318	The shallow compensating donors in molecular beam epitaxy grown ZnSe:N. Solid State Communications, 1996, 97, 909-912.	1.9	6
319	Optical gain characteristics and excitonic nonlinearities in IIâ€VI laser diodes. Journal of Crystal Growth, 1998, 184-185, 575-579.	1.5	6
320	Temperature-dependent measurements on ZnSe heterostructures by high-resolution X-ray diffraction. Journal of Crystal Growth, 1998, 184-185, 100-104.	1.5	6
321	Thermally induced strain in MBE grown GaN layers. Journal of Crystal Growth, 1998, 189-190, 375-379.	1.5	6
322	Lateral index guiding in ZnCdSe quantum well lasers by selective implantation-induced disordering. Applied Physics Letters, 1998, 73, 1865-1867.	3.3	6
323	Influence of Doping on the Lattice Dynamics of Gallium Nitride. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	6
324	Characterization of optical induced defect-band-transitions in MBE grown galliumnitride by optical admittance spectroscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 226-229.	3.5	6

#	ARTICLE	IF	CITATIONS
325	Homoepitaxial laser diodes grown on conducting and insulating ZnSe substrates. Journal of Crystal Growth, 1999, 201-202, 933-937.	1.5	6
326	High-Power Operation of ZnSe-Based cw-Laser Diodes. Physica Status Solidi A, 2000, 180, 21-26.	1.7	6
327	Shallow donors in ultrathin nitrogen-doped ZnSe layers – a novel or a disregarded compensation mechanism in II–VI device structures?. Journal of Crystal Growth, 2000, 214-215, 497-501.	1.5	6
328	Low threshold current densities for II-VI lasers. Electronics Letters, 2000, 36, 878.	1.0	6
329	On the dynamics of InGaN dot formation by RF-MBE growth. Materials Research Society Symposia Proceedings, 2004, 831, 323.	0.1	6
330	The role of sub-contact layers in the optimization of low-resistivity contacts to p-type GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2537-2540.	0.8	6
331	Microscopic emission properties of nonpolar a -plane GaN grown by HVPE. , 2006, , .		6
332	Metastability of the UV luminescence in Mg-doped GaN layers grown by MOVPE on quasi-bulk GaN templates. Physica B: Condensed Matter, 2007, 401-402, 302-306.	2.7	6
333	Deep ridge GaN cw-laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 78-81.	0.8	6
334	Characterization of growth defects in thin GaN layers with X-ray microbeam. Physica Status Solidi (B): Basic Research, 2007, 244, 1735-1742.	1.5	6
335	Absorption and emission of polariton modes in a ZnSe–ZnSSe heterostructure. Physica Status Solidi (B): Basic Research, 2008, 245, 1093-1097.	1.5	6
336	Blue monolithic II-VI-based vertical-cavity surface-emitting laser. Applied Physics Letters, 2012, 100, 121102.	3.3	6
337	Determination of the Fermi level position in dilute magnetic Ga _{1-x} Mn _x N films. Journal of Applied Physics, 2014, 115, 123706.	2.5	6
338	GaN tubes with coaxial non– and semipolar GaInN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 648-651.	0.8	6
339	Emission dynamics of hybrid plasmonic gold/organic GaN nanorods. Nanotechnology, 2017, 28, 505710.	2.6	6
340	Piezomodulated reflectivity on CdMnTe/CdTe quantum well structures as a new standard characterization method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 16, 92-95.	3.5	5
341	Correlation between electrical and structural properties of chlorine doped ZnSe epilayers grown by molecular beam epitaxy. Journal of Crystal Growth, 1994, 138, 331-337.	1.5	5
342	Absorption as Optical Access to Acceptor Concentrations and Compensation Mechanism in ZnSe Epilayers. Materials Science Forum, 1995, 182-184, 259-262.	0.3	5

#	ARTICLE	IF	CITATIONS
343	Propagation of exciton polaritons in. Journal of Crystal Growth, 1996, 159, 800-804.	1.5	5
344	Shubnikov-de Haas oscillations of a two-dimensional electron gas in a modulation-doped single quantum well. Solid State Communications, 1996, 100, 739-742.	1.9	5
345	Low damage thermally assisted electron cyclotron resonance etch technology for wide bandgap II-VI materials. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 2656.	1.6	5
346	Investigation of the interfacial quality and the influence of different substrates in ZnSe homoepitaxy. Journal of Crystal Growth, 1997, 174, 751-756.	1.5	5
347	Doping-dependent Mg diffusion in ZnMgSSe/ZnSSe-structures. Journal of Crystal Growth, 1998, 184-185, 465-469.	1.5	5
348	Structural properties of homoepitaxial and heteroepitaxial ZnSe-based laser structures. Journal of Crystal Growth, 1998, 184-185, 587-590.	1.5	5
349	Defect Complexes in Highly Mg-Doped GaN Studied by Raman Spectroscopy. Physica Status Solidi (B): Basic Research, 1999, 216, 551-555.	1.5	5
350	Incorporation of Deep Defects in GaN Induced by Doping and Implantation Processes. Physica Status Solidi (B): Basic Research, 1999, 216, 587-591.	1.5	5
351	Dynamics of Excitons and Biexcitons in One Single Quantum Dot. Physica Status Solidi (B): Basic Research, 2000, 221, 25-29.	1.5	5
352	Generation of misfit dislocations due to thermally induced strain $\hat{\epsilon}$ a study by temperature-dependent HRXRD. Journal of Crystal Growth, 2000, 214-215, 447-451.	1.5	5
353	Growth of (Zn)CdSe quantum structures on vicinal GaAs(001) substrates: step flow growth versus strain effects. Journal of Crystal Growth, 2000, 214-215, 606-609.	1.5	5
354	Influence of driving conditions on the stability of ZnSe-based cw-laser diodes. Journal of Crystal Growth, 2000, 214-215, 1040-1044.	1.5	5
355	Gyromagnetic ratios of electrons confined in quantum wells in $\text{ZnSe}/\text{Zn}_x\text{Mg}_{1-x}\text{Se}_y$ heterostructures. Physical Review B, 2000, 62, 10329-10334.	3.2	5
356	New laser sources for plastic optical fibers: ZnSe-based quantum well and quantum dot laser diodes with 560-nm emission. , 2001, 4594, 260.		5
357	Single-photon and photon-pair emission from CdSe/Zn(S,Se) quantum dots. Physica Status Solidi (B): Basic Research, 2003, 238, 321-324.	1.5	5
358	Cathodoluminescence and atomic force microscopy study of n-type doped GaN epilayers. Physica Status Solidi A, 2004, 201, 212-215.	1.7	5
359	Novel ZnTe-based green light emitters grown on ZnTe substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1010-1013.	0.8	5
360	Surface segregation of Si and Mg dopants in MOVPE grown GaN films revealed by X-ray photoemission spectro-microscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1725-1728.	0.8	5

#	ARTICLE	IF	CITATIONS
361	Phonons in strained AlGa _N /Ga _N superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 170-174.	0.8	5
362	Optical properties of single and multi-layer InGa _N quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1883-1885.	0.8	5
363	Optical properties of Ga _N nanorods grown catalyst-free on α -plane sapphire. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S578.	0.8	5
364	Optical properties and modal gain of InGa _N quantum dot stacks. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S590-S593.	0.8	5
365	Electroluminescence from InGa _N quantum dots in a fully monolithic Ga _N /AlIn _N cavity. <i>Journal of Crystal Growth</i> , 2011, 320, 28-31.	1.5	5
366	Influence of a low-temperature capping on the crystalline structure and morphology of InGa _N quantum dot structures. <i>Journal of Alloys and Compounds</i> , 2014, 585, 572-579.	5.5	5
367	Photonic Crystal Structures Based on Ga _N Ultrathin Membranes. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2014, 9, 271-275.	0.5	5
368	Emission and material gain spectra of polar compressive strained AlGa _N quantum wells grown on virtual AlGa _N substrates: Tuning emission wavelength and mixing TE and TM mode of light polarization. <i>Semiconductor Science and Technology</i> , 2018, 33, 075003.	2.0	5
369	Crystal field model simulations of magnetic response of pairs, triplets and quartets of Mn ³⁺ ions in Ga _N . <i>New Journal of Physics</i> , 2020, 22, 123016.	2.9	5
370	Toward Better Light-Confinement in Micropillar Cavities. <i>Acta Physica Polonica A</i> , 2011, 120, 877-879.	0.5	5
371	The Influence of Oxygen and Carbon Contaminants on the Valence Band of p-Ga _N (0001). <i>Acta Physica Polonica A</i> , 2019, 136, 585-588.	0.5	5
372	Thermoluminescence mechanism in CdF ₂ :Eu. <i>Physical Review B</i> , 1992, 46, 7395-7406.	3.2	4
373	Structural and electrical properties of ZnSe laser diodes optimized by transmission electron microscopy, reflection high energy electron diffraction, X-ray diffraction and C-V profiling. <i>Journal of Crystal Growth</i> , 1995, 150, 743-748.	1.5	4
374	Zeeman Spectroscopy on the Nitrogen Acceptor-Bound Exciton in Epitaxial ZnSe. <i>Materials Science Forum</i> , 1995, 182-184, 303-306.	0.3	4
375	Modulator and saturable absorber for integration with CdZnSe/ZnSe/ZnMgSSe QW-laser diodes. <i>Journal of Crystal Growth</i> , 1996, 159, 893-897.	1.5	4
376	Raman signals and phonon sidebands under resonant excitation of donor - acceptor-pair states: spectroscopy with enhanced sensitivity to local vibrational excitations. <i>Semiconductor Science and Technology</i> , 1996, 11, 1255-1262.	2.0	4
377	MBE Growth of Ga _N on NdGaO ₃ (101). <i>Materials Research Society Symposia Proceedings</i> , 1997, 482, 364.	0.1	4
378	Optical Spectroscopy of Mg- and C-Related Donor and Acceptor Levels in Ga _N Grown by MBE. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 216, 557-560.	1.5	4

#	ARTICLE	IF	CITATIONS
379	Green emitting DFB laser diodes based on ZnSe. Electronics Letters, 1999, 35, 718.	1.0	4
380	Spin-Dependent Exciton-Exciton Interaction in ZnSe Quantum Wells. Physica Status Solidi A, 2000, 178, 535-538.	1.7	4
381	Correlated Temporal Fluctuations and Random Intermittency of Optical Transitions in a Single Quantum Dot. Physica Status Solidi (B): Basic Research, 2001, 224, 201-205.	1.5	4
382	Defect properties of ion-implanted nitrogen in ZnSe. Physical Review B, 2001, 63, .	3.2	4
383	Studies of Misfit Dislocation Densities in II-VI Laser Structures by Diffuse X-Ray Scattering. Physica Status Solidi (B): Basic Research, 2002, 229, 193-196.	1.5	4
384	Negatively Charged Donor Centers in Ultrathin ZnSe:N Layers. Physica Status Solidi (B): Basic Research, 2002, 229, 245-250.	1.5	4
385	Displaced Substitutional Phosphorus Acceptors in Zinc Selenide. Physica Status Solidi (B): Basic Research, 2002, 229, 257-260.	1.5	4
386	Pyramidal Defect Formation in View of Magnesium Segregation. Physica Status Solidi A, 2002, 192, 456-460.	1.7	4
387	Coupling of optical modes in GaN-based laser-diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2287-2291.	0.8	4
388	Wafer Bonding of GaN and ZnSse for Optoelectronic Applications. Japanese Journal of Applied Physics, 2004, 43, L1275-L1277.	1.5	4
389	Nondestructive evaluation of misfit dislocation densities in ZnSe-GaAs heterostructures by x-ray diffuse scattering. Journal of Applied Physics, 2005, 97, 103506.	2.5	4
390	Study on electrical properties of II-VI-based distributed Bragg reflectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1217-1220.	0.8	4
391	Two to three dimensional transitions of InGaN and the impact of GaN overgrowth. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1396-1399.	0.8	4
392	Optical properties of single InGaN quantum dots up to 150 K. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3864-3868.	0.8	4
393	Characterization of crystallographic properties and defects via X-ray microdiffraction in GaN (0001) layers. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 142-148.	1.8	4
394	Strain in-plane GaN layers grown on-plane sapphire substrates. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1672-1675.	1.8	4
395	Assessment of phonon mode characteristics via infrared spectroscopic ellipsometry on-plane GaN. Physica Status Solidi (B): Basic Research, 2006, 243, 1594-1598.	1.5	4
396	Phase sensitive spectroscopy of the polariton modes in a ZnSe-ZnSxSe1-x heterostructure. Solid State Communications, 2006, 138, 457-460.	1.9	4

#	ARTICLE	IF	CITATIONS
397	Two-step growth of InGaN quantum dots and application to light emitters. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2407-2410.	0.8	4
398	Distributed Bragg reflectors in comparison to RUGATE and nested super lattices – growth, reflectivity, and conductivity. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1839-1842.	0.8	4
399	Mapping strain gradients in the FIB-structured InGaN/GaN multilayered films with 3D X-ray microbeam. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2010, 528, 52-57.	5.6	4
400	Radiative recombination in photoexcited quantum dots up to room temperature: The role of fine-structure effects. <i>Physical Review B</i> , 2010, 81, .	3.2	4
401	Catalyst free self-organized grown high-quality GaN nanorods. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1787-1799.	1.5	4
402	Microstructural and compositional analyses of GaN-based nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1822-1836.	1.5	4
403	Contactless electroreflectance study of the surface potential barrier in <i>n</i> -type and <i>p</i> -type InAlAs van Hoof structures lattice matched to InP. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 215104.	2.8	4
404	Verification of threading dislocations density estimation methods suitable for efficient structural characterization of Al _x Ga _{1-x} N/GaN heterostructures grown by MOVPE. <i>Journal of Applied Physics</i> , 2019, 126, 165304.	2.5	4
405	Comparison of Exciton Properties in Quantum Well Structures of ZnCdSe/ZnSe and ZnSe/ZnMgSSe. <i>Acta Physica Polonica A</i> , 1998, 94, 313-316.	0.5	4
406	Detailed surface studies on the reduction of Al incorporation into AlGaN grown by molecular beam epitaxy in the Ga-droplet regime. <i>Vacuum</i> , 2022, 202, 111168.	3.5	4
407	Electroluminescence of Schottky diodes rare-earth-doped zinc sulphide. <i>Semiconductor Science and Technology</i> , 1987, 2, 112-115.	2.0	3
408	The influence of II-VI lattice damage on rare earth sites as determined by site selective spectroscopy and cathodoluminescence: argon implanted ZnS:Sm ³⁺ . <i>Journal of Luminescence</i> , 1992, 52, 325-334.	3.1	3
409	Blau-grünes Licht von ZnSe-Laserdioden. <i>Physik Journal</i> , 1994, 50, 160-162.	0.1	3
410	Gain mechanisms in exciton-localizing ZnSe-based quantum well structures. , 1995, 2362, 515.		3
411	Bleaching of excitonic absorption in II-VI laser diodes under lasing conditions. <i>Journal of Crystal Growth</i> , 1996, 159, 661-666.	1.5	3
412	Correlation between crystal defects and the band gap of epitaxially grown Hg _{1-x} Zn _x Se on GaAs(001). <i>Journal of Crystal Growth</i> , 1996, 159, 1123-1127.	1.5	3
413	Deep Trap Characterization In GaN Using Thermal And Optical Admittance Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 1997, 482, 892.	0.1	3
414	Biexcitons in Low-Dimensional CdZnSe/ZnSe Structures. <i>Physica Status Solidi A</i> , 1997, 164, 205-208.	1.7	3

#	ARTICLE	IF	CITATIONS
415	Electroabsorption in low-dimensional and bulk-like Zn _{1-x} Cd _x Se. Journal of Crystal Growth, 1998, 184-185, 706-709.	1.5	3
416	Optical Admittance Spectroscopy of Deep Centers in Galliumnitride - Correlation with Photoluminescence. Materials Science Forum, 1998, 264-268, 1381-1384.	0.3	3
417	Optimised Implantation-Induced Disorder for Lowering the Threshold Current Density of II-VI Laser Diodes. Physica Status Solidi A, 2000, 180, 213-216.	1.7	3
418	Low threshold II-VI laser diodes with transversal and longitudinal single-mode emission. Journal of Crystal Growth, 2000, 214-215, 1045-1048.	1.5	3
419	Lateral-index-guided ZnCdSSe lasers. Journal of Crystal Growth, 2000, 214-215, 1054-1057.	1.5	3
420	Infrared spectroscopic ellipsometry for nondestructive characterization of free-carrier and crystal-structure properties of group-III-nitride semiconductor device heterostructures. , 2001, , .		3
421	Growth of ZnCdSe quantum wells at low substrate temperatures using migration enhanced epitaxy. Journal of Crystal Growth, 2001, 227-228, 650-654.	1.5	3
422	Influence of capping conditions on structural properties of CdSe/ZnSe quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1208-1211.	2.7	3
423	Optical properties of epitaxially grown submonolayerCdSe-ZnSenanostructures. Physical Review B, 2004, 70, .	3.2	3
424	Comparative Study of GaN Based Light Emitting Devices Grown on Sapphire and GaN Substrates. Materials Research Society Symposia Proceedings, 2004, 831, 194.	0.1	3
425	Influence of the cap layer growth temperature on the Cd distribution in CdSe/ZnSe heterostructures. Journal of Crystal Growth, 2004, 263, 348-352.	1.5	3
426	High stability of CdZnSSe active layers in ZnSe-based laser diodes by introducing strain-compensating barrier layers. Physica Status Solidi (B): Basic Research, 2004, 241, 727-730.	1.5	3
427	Microstructural study of quantum well degradation in ZnSe-based laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1005-1009.	0.8	3
428	Influence of n-type doping on light emission properties of GaN layers and GaN-based quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1056-1059.	0.8	3
429	Microstructural and Optical Evaluation of Nitride Light-Emitting Diodes and II-VI Distributed Bragg Reflectors Combined by Direct Wafer Bonding. Japanese Journal of Applied Physics, 2005, 44, L958-L960.	1.5	3
430	Anisotropic spatial correlation of CdSe/Zn(S)Se quantum dot stacks grown by MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 887-890.	0.8	3
431	Bending in HVPE GaN free-standing films: effects of laser lift-off, polishing and high-pressure annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1475-1478.	0.8	3
432	Phase resolved polariton interferences in a ZnSe-ZnSSe heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2453-2456.	0.8	3

#	ARTICLE	IF	CITATIONS
433	Efficient coupling into confined optical modes of ZnSe-based pillar microcavities. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 844-848.	1.5	3
434	Spectro-microscopy of Si doped GaN films. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 246, 79-84.	1.4	3
435	Concentration Measurement In Free-Standing InGaN Nano-Islands With Transmission Electron Microscopy. <i>Microscopy and Microanalysis</i> , 2007, 13, 312-313.	0.4	3
436	On the way to InGaN quantum dots embedded into monolithic nitride cavities. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 1806-1809.	1.5	3
437	Room temperature emission from CdSe single quantum dots embedded in high bandgap barrier material. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1938-1940.	2.7	3
438	Influence of piezoelectric fields on excitonic complexes in InGaN quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 872-875.	0.8	3
439	Transmission electron microscopical investigation of AlGaIn/GaN distributed Bragg reflectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S680.	0.8	3
440	Influence of doping on optical properties of catalyst- and mask-free grown gallium nitride nanorods. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2240-2242.	0.8	3
441	On the structural properties of MgS-rich II-VI-based microcavities. <i>Journal of Crystal Growth</i> , 2013, 378, 270-273.	1.5	3
442	The impact of nanoporation on persistent photoconductivity and optical quenching effects in suspended GaN nanomembranes. <i>Applied Physics Letters</i> , 2013, 103, 243113.	3.3	3
443	Colour and multicolour tuning of InGaN quantum dot based light-emitting diodes. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 055108.	2.8	3
444	Bragg polaritons in a ZnSe-based unfolded microcavity at elevated temperatures. <i>Applied Physics Letters</i> , 2016, 108, 121105.	3.3	3
445	Electrical characteristics of vertical-geometry Schottky junction to magnetic insulator (Ga,Mn)N heteroepitaxially grown on sapphire. <i>Journal of Alloys and Compounds</i> , 2019, 804, 415-420.	5.5	3
446	Material Gain Engineering in Staggered Polar AlGaIn/AlN Quantum Wells Dedicated for Deep UV Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2019, 25, 1-8.	2.9	3
447	Raman scattering studies of the lateral Mn distribution in MBE-grown Ga1-Mn N epilayers. <i>Journal of Alloys and Compounds</i> , 2020, 817, 152789.	5.5	3
448	Growth and properties of the GaN cap layer strongly influenced by the composition of the underlying AlGaIn. <i>Materials Science in Semiconductor Processing</i> , 2021, 136, 106125.	4.0	3
449	Analysis of the Defect Structure of Epitaxial GaN. <i>Physica Status Solidi A</i> , 1999, 176, 391-395.	1.7	3
450	Cathodoluminescence Profiling of InGaN-Based Quantum Well Structures and Laser Diodes - In-Plane Instabilities of Light Emission. <i>Acta Physica Polonica A</i> , 2003, 103, 689-694.	0.5	3

#	ARTICLE	IF	CITATIONS
451	Comparison of Long-Time Delay in Lasing in Homo- and Heteroepitaxially Grown II-VI Laser Diodes. Acta Physica Polonica A, 1998, 94, 355-358.	0.5	3
452	Recombination in deep etched CdZnSe/ZnSe quantum wires. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1729-1733.	0.4	2
453	Coherent dynamics of free and bound excitons in strained ZnSe epilayers. Journal of Luminescence, 1995, 66-67, 478-482.	3.1	2
454	Degenerate-Four-Wave-Mixing at the Nitrogen Acceptor Bound Exiton in ZnSe Epilayers. Materials Science Forum, 1995, 182-184, 283-286.	0.3	2
455	Gain-coupled distributed feedback lasers in the blue-green spectral range by focused ion beam implantation. Journal of Crystal Growth, 1996, 159, 591-594.	1.5	2
456	Hole trap generation by thermal treatment of nitrogen doped p-type ZnSe on GaAs characterized by deep level transient spectroscopy. Applied Physics Letters, 1997, 71, 2187-2189.	3.3	2
457	Nitrogen Doped ZnSe Layers on GaAs. Physica Status Solidi (B): Basic Research, 1997, 202, 895-901.	1.5	2
458	Hot exciton relaxation in CdZnSe/ZnSe quantum wells and quantum dots. Journal of Crystal Growth, 1998, 184-185, 330-333.	1.5	2
459	Influence of Activated Nitrogen on Plasma Assisted MBE Growth of GaN. Materials Science Forum, 1998, 264-268, 1193-1196.	0.3	2
460	Studies on Carbon as Alternative P-Type Dopant for Gallium Nitride. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
461	Influence of Doping on the Lattice Dynamics of Gallium Nitride. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 327-332.	1.0	2
462	On the Impact of Microstructure on Luminescence of InGaN/GaN Multi Quantum Wells Grown by Molecular Beam Epitaxy. Physica Status Solidi A, 1999, 176, 291-295.	1.7	2
463	Thermally Induced Strain in ZnSe and GaN Epitaxial Layers Studied by High-Resolution X-Ray Diffraction at Variable Temperatures. Physica Status Solidi A, 2000, 180, 189-194.	1.7	2
464	Stacking-fault-induced pairs of localizing centers in ZnSe quantum wells. Journal of Crystal Growth, 2000, 214-215, 634-638.	1.5	2
465	Current spreading in AlGaIn:Mg cladding layers of laser structures. Materials Research Society Symposia Proceedings, 2001, 693, 162.	0.1	2
466	Determination of band offset using continuous-wave two-photon excitation in a ZnSe quantum-well waveguide structure. Physical Review B, 2001, 63, .	3.2	2
467	Direct observation of all-optical injection of spin-polarized currents. Physica Status Solidi (B): Basic Research, 2003, 238, 548-551.	1.5	2
468	Curvature and strain in thick HVPE-GaN for quasi-substrate applications. Materials Research Society Symposia Proceedings, 2003, 798, 350.	0.1	2

#	ARTICLE	IF	CITATIONS
469	Investigation of CdSe/ZnS quantum dot ordering by grazing incidence small angle X-ray scattering. <i>Physica Status Solidi (B): Basic Research</i> , 2004, 241, 523-526.	1.5	2
470	Structural investigations of spatial correlation of CdSe/ZnSe quantum dot stacks grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2005, 278, 316-319.	1.5	2
471	Characterization and structuring of nitride-based heterostructures for vertical-cavity surface-emitting lasers. , 2005, , 79-82.		2
472	CdSe/ZnSe quantum dots coupled to modes of monolithic II-VI pillar microcavities: tunability and Purcell effect. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 3680-3684.	0.8	2
473	Profiling of light emission of GaN-based laser diodes with cathodoluminescence. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 1811-1814.	1.8	2
474	Crack free monolithic nitride vertical-cavity surface-emitting laser structures and pillar microcavities. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 1749-1753.	1.8	2
475	Coherent exciton-LO-phonon polarons in ZnSe quantum wells with strong confinement. <i>Physical Review B</i> , 2007, 75, .	3.2	2
476	InGaN Selfassembled Quantum Dots Investigated By X-Ray Diffraction-Anomalous-Fine Structure Technique. <i>AIP Conference Proceedings</i> , 2007, , .	0.4	2
477	Wide-Bandgap Quantum Dot Based Microcavity VCSEL Structures. , 2008, , 29-41.		2
478	Emission properties of ZnSe-based pillar microcavities at elevated temperatures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 508-511.	0.8	2
479	Radiative recombination dynamics of CdSe/Zn(S,Se)/MgS quantum dots up to room temperature. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1413-1415.	1.5	2
480	Microphotoluminescence studies on GaN-based airpost pillar microcavities containing InGaN quantum wells and quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1756-1764.	1.5	2
481	Band engineering in nitrogen-rich AlGaInAs quaternary alloys. <i>Vacuum</i> , 2021, 189, 110240.	3.5	2
482	ZnCdSe Quantum Structures " Growth, Optical Properties and Applications. , 2002, , 27-37.		2
483	Light Emission Properties of GaN-Based Laser Diode Structures. <i>Acta Physica Polonica A</i> , 2005, 108, 675-680.	0.5	2
484	Enhanced Exciton-Phonon Interaction in Strained ZnCdSe/ZnSe Quantum Well Structures. <i>Acta Physica Polonica A</i> , 1997, 92, 769-773.	0.5	2
485	Properties and Prospects of ZnSe-Based Quantum Dot Microcavity VCSEL Structures. <i>Journal of the Korean Physical Society</i> , 2008, 53, 83-87.	0.7	2
486	Influence of pulsed Al deposition on quality of Al-rich Al(Ga)N structures grown by molecular beam epitaxy. <i>Surfaces and Interfaces</i> , 2021, 27, 101560.	3.0	2

#	ARTICLE	IF	CITATIONS
487	X-ray diffraction studies of residual strain in AlN/sapphire templates. Measurement: Journal of the International Measurement Confederation, 2022, 200, 111611.	5.0	2
488	Energy transfer processes in rare earth doped ZnS under non-linear excitation. Journal of Crystal Growth, 1992, 117, 721-726.	1.5	1
489	First evidence of Shubnikov-De Haas oscillations in CdTe. Physica B: Condensed Matter, 1993, 184, 226-228.	2.7	1
490	<title>Ultrafast differential-transmission spectroscopy of excitons in strained ZnSe layers and Zn _{1-x} Cd _x Se/ZnSe quantum wells</title>., 1995, 2362, 74.		1
491	Coherent effects in nonlinear absorption of thin ZnSe layers and Zn _{1-x} Cd _x Se/ZnSe quantum wells under resonant excitation. Journal of Luminescence, 1995, 66-67, 65-69.	3.1	1
492	Excitonic Processes in Highly Excited Zn _{1-x} Cd _x Se/ZnSe and CdSe/ZnSe Single and Multiple Quantum Wells. Materials Science Forum, 1995, 182-184, 183-186.	0.3	1
493	Analytical Model for Calculating Exciton Energies as Measured in Zn _{1-x} Cd _x Se/ZnSe and ZnSe/ZnS _{1-x} Se _x /ZnSe Quantum Wells. Materials Science Forum, 1995, 182-184, 191-194.	0.3	1
494	Optically Defected Cyclotron Resonance Investigation of Epitaxially Grown ZnSe. Materials Science Forum, 1995, 182-184, 307-310.	0.3	1
495	Defect Related Recombination Processes in II-VI Quantum Wells. Materials Science Forum, 1995, 196-201, 455-460.	0.3	1
496	A comparison of Mg and Ca for quaternary cladding layers in ZnSe based laser diodes. Journal of Crystal Growth, 1996, 159, 32-35.	1.5	1
497	Optimization of the waveguide properties for ZnSe laser diodes. Journal of Crystal Growth, 1996, 159, 623-627.	1.5	1
498	Picosecond lasing dynamics of gain-switched (Zn,Cd)Se/Zn(S,Se)/(Zn,Mg)(S,Se) quantum well lasers. Journal of Applied Physics, 1997, 82, 548-551.	2.5	1
499	Defect-Related Recombination Processes in Low-Dimensional Structures of ZnCdSe/ZnSe, CdTe/CdMnTe and GaAs/AlGaAs. Materials Science Forum, 1997, 258-263, 1665-1670.	0.3	1
500	Determination of the Lattice Site of Nitrogen after Implantation into ZnSe. Materials Science Forum, 1997, 258-263, 1395-1400.	0.3	1
501	Hot excitons in ZnSe quantum wells. Journal of Luminescence, 1997, 72-74, 292-293.	3.1	1
502	Electrical transport and trap properties in nitrogen-doped p-type MBE-grown ZnSe layers on GaAs using different contact materials. Journal of Crystal Growth, 1998, 184-185, 440-444.	1.5	1
503	¹⁵ N-NMR on implanted boron and nitrogen in ZnSe. Journal of Crystal Growth, 1998, 184-185, 485-489.	1.5	1
504	Stability issues of quaternary CdZnS ₂ Se and ternary CdZnSe quantum wells in blue-green laser diodes. Journal of Crystal Growth, 1998, 184-185, 580-584.	1.5	1

#	ARTICLE	IF	CITATIONS
505	Migration enhanced epitaxy of CdSe islands on ZnSe and their optical and structural characterization. <i>Microelectronic Engineering</i> , 1998, 43-44, 701-705.	2.4	1
506	Relaxation of hot excitons in CdZnSe/ZnSe quantum wells and quantum dots. <i>Superlattices and Microstructures</i> , 1998, 23, 1093-1096.	3.1	1
507	Direct Imaging of the Crystalline and Chemical Nanostructure of Ga,In-Nitrides by Highly Spatially-, Spectrally- and Time-Resolved Cathodoluminescence. <i>Solid State Phenomena</i> , 1998, 63-64, 221-228.	0.3	1
508	Growth Evolution of (Zn,Cd)Se Quantum Dots Deduced from Spatially Resolved Structural and Optical Characterization. <i>Materials Research Society Symposia Proceedings</i> , 1999, 571, 325.	0.1	1
509	Localization of Excitons in Pairs of Natural Dots Induced by Stacking Faults in ZnSe Quantum Wells. <i>Physica Status Solidi A</i> , 2000, 178, 189-192.	1.7	1
510	Spin and exchange effects in CdSe/ZnSe quantum dots probed by single-dot spectroscopy. <i>Journal of Crystal Growth</i> , 2000, 214-215, 737-741.	1.5	1
511	The trion spin-singlet and -triplet states in ZnSe single quantum wells. <i>Journal of Crystal Growth</i> , 2000, 214-215, 832-836.	1.5	1
512	Investigation of Green Emitting Monolithic II-VI Vertical Cavity Surface Emitting Laser. <i>Materials Research Society Symposia Proceedings</i> , 2002, 722, 471.	0.1	1
513	Optical evaluation of pretreated InGaN quantum well structures. <i>Materials Research Society Symposia Proceedings</i> , 2003, 798, 598.	0.1	1
514	High pressure annealing of HVPE GaN free-standing films: redistribution of defects and stress. <i>Materials Research Society Symposia Proceedings</i> , 2004, 831, 49.	0.1	1
515	Defect characterization of electrically degraded ZnSe based laser diodes. <i>Physica Status Solidi A</i> , 2004, 201, R28-R30.	1.7	1
516	Direct investigation of very thin CdSe layers on ZnSe by out-of-plane grazing incidence X-ray diffraction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 702-705.	0.8	1
517	Microphotoluminescence of strongly localized states in InGaN/GaN layers - emission of quantum dots?. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2744-2747.	0.8	1
518	X-ray standing wave investigations of Si dopant incorporation in GaN. <i>Materials Research Society Symposia Proceedings</i> , 2005, 892, 29.	0.1	1
519	Epitaxial growth of InGaN quantum dots grown by MOVPE: Effect of capping process on the structural and optical properties. <i>Materials Research Society Symposia Proceedings</i> , 2005, 892, 178.	0.1	1
520	Growth and formation of InGaN and GaN nano-structures studied by STM. <i>E-Journal of Surface Science and Nanotechnology</i> , 2006, 4, 90-95.	0.4	1
521	Growth and morphology of MOVPE grown InGaN/GaN islands. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1557-1560.	0.8	1
522	Structural investigations of GaN films with X-ray standing waves. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1729-1732.	0.8	1

#	ARTICLE	IF	CITATIONS
523	Novel devices based on the combination of nitride and II-VI materials. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1771-1777.	1.8	1
524	Mapping misorientation and crystallographic tilt in GaN layers via polychromatic microdiffraction. Physica Status Solidi (B): Basic Research, 2006, 243, 1508-1513.	1.5	1
525	Bending in HVPE grown GaN films: origin and reduction possibilities. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2256-2259.	0.8	1
526	Micro-analysis of light emission properties of GaN-based laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2818-2821.	0.8	1
527	Wave guide optimization for homoepitaxial laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2842-2845.	0.8	1
528	Low-temperature growth of InGaN/GaN nano-islands investigated by grazing-incidence X-ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S602.	0.8	1
529	Local structure of uncapped and capped InGaN/GaN quantum dots. Journal of Synchrotron Radiation, 2009, 16, 494-497.	2.4	1
530	Electrically driven room temperature operation of a single quantum dot emitter. , 2009, , .		1
531	Electroluminescence from isolated single indium gallium nitride quantum dots up to 150%K. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1428-1430.	1.8	1
532	Polarized light emission from CdSe/ZnSSe quantum-dot monolithic pillar microcavities. Journal of Physics: Conference Series, 2010, 245, 012058.	0.4	1
533	Influence of growth imperfections on optical properties of nitride pillar VCSEL microcavities. Physica Status Solidi (B): Basic Research, 2011, 248, 1867-1870.	1.5	1
534	Optical properties of wide-bandgap monolithic pillar microcavities with different geometries. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1246-1249.	0.8	1
535	Growth of II-VI and III-nitride quantum-dot microcavity systems. , 2012, , 447-484.		1
536	Blue lasing and strong coupling in ZnSe monolithic microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1230-1233.	0.8	1
537	Tamm plasmon polaritons in the visible spectral region and its optical properties in ZnSe-based microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 498-502.	0.8	1
538	Polarity dependence of Mn incorporation in (Ga,Mn)N superlattices. Journal of Crystal Growth, 2016, 437, 49-52.	1.5	1
539	Structural and electrical properties of Pd/p-GaN contacts for GaN-based laser diodes. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, 032211.	1.2	1
540	Relationship between Sample Morphology and Carrier Diffusion Length in GaN Thin Films. Acta Physica Polonica A, 2002, 102, 627-632.	0.5	1

#	ARTICLE	IF	CITATIONS
541	Optical Properties and Microstructure of InGaN Grown by Molecular Beam Epitaxy. Acta Physica Polonica A, 1998, 94, 260-264.	0.5	1
542	Optical Properties of Molecular Beam Epitaxy Grown ZnSe on GaAs. Acta Physica Polonica A, 1993, 84, 551-554.	0.5	1
543	Influence of Growth Conditions on Optical Properties of ZnCdSe/ZnSe Quantum Wells Grown by Molecular Beam Epitaxy. Acta Physica Polonica A, 1996, 90, 785-788.	0.5	1
544	Infections tropicales graves dans les départements français d'Amérique, Antilles françaises et Guyane. Medecine Intensive Reanimation, 2019, 28, 202-216.	0.0	1
545	Improved conductivity measurement of semiconductor epitaxial layers by means of the contactless microwave method. , 1994, 2211, 649.		0
546	Molecular-beam-epitaxial growth and characterization of $Zn_{1-x}CaxSySe_{1-y}$ alloys for blue-green laser applications. Journal of Applied Physics, 1996, 79, 763.	2.5	0
547	Efficient lateral index guiding of II-VI laser structures by implantation-induced disordering. Journal of Crystal Growth, 1998, 184-185, 566-570.	1.5	0
548	Spectro-temporal gain dynamics of optically pumped II-VI multiple-quantum-well structures. Journal of Crystal Growth, 1998, 184-185, 637-640.	1.5	0
549	Quantum Interference Effects in Highly Doped n-ZnSe Epitaxy Layers Grown by MBE. Physica Status Solidi (B): Basic Research, 1998, 206, 575-582.	1.5	0
550	Frequency selective Bragg filters based on (Mg,Zn) (S,Se) waveguides for the visible spectral range. IEEE Photonics Technology Letters, 1998, 10, 1130-1132.	2.5	0
551	Statistical Analysis of Local Composition and Luminescence in InGaN Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
552	Investigations of ZnSe based laser structures on ZnSe substrates by high resolution x-ray diffraction. Journal Physics D: Applied Physics, 1999, 32, A47-A50.	2.8	0
553	Electroabsorption studies on quasi-three-dimensional and quasi-two-dimensional excitons in (Zn,Cd)Se/Zn(S,Se) structures. Journal of Applied Physics, 1999, 86, 4360-4364.	2.5	0
554	Electron-phonon quantum kinetics in the strong coupling regime. Journal of Luminescence, 1999, 83-84, 155-160.	3.1	0
555	Influence of Carbon Doping on the Photoconductivity in GaN Layers. Physica Status Solidi (B): Basic Research, 1999, 216, 593-597.	1.5	0
556	Gain characteristics of ZnSe/(Zn,Mg)(S,Se)/(Zn,Mg)(S,Se) quantum well lasers. , 1999, , .		0
557	Thermal Expansion of GaN at Low Temperatures - a Comparison of Bulk and Homo- and Heteroepitaxial Layers. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	0
558	Eigenstate symmetry probed by biexciton transitions in a single quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 350-353.	2.7	0

#	ARTICLE	IF	CITATIONS
559	A new approach to improved green emitting II-VI laser diodes. , 0, , .		0
560	Mg related Defect Formation during MOVPE Growth of GaN based Films studied by Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 2001, 693, 110.	0.1	0
561	<title>Spectral diffusion and fine structure splitting of optical transitions in semiconductor quantum dots</title>. , 2001, 4318, 1.		0
562	Compositional Fluctuations in Al _x Ga _{1-x} N Layers grown on 6H-SiC (0001) by Metal Organic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2002, 743, L3.51.1.	0.1	0
563	TEM investigation of defect reduction and etch pit formation in GaN. Materials Research Society Symposia Proceedings, 2003, 798, 484.	0.1	0
564	Direct observation of optically injected spin-polarized currents in semiconductors. , 2003, , .		0
565	Microstructural Evaluation of Compositional Fluctuations in AlGa _N Grown on 6H-SiC Substrates. Microscopy and Microanalysis, 2003, 9, 256-257.	0.4	0
566	Microstructure of highly p-type doped GaN sub-contact layers for low-resistivity contacts. Materials Research Society Symposia Proceedings, 2004, 831, 603.	0.1	0
567	Micro-photoluminescence studies of excitonic and multiexcitonic states of quantum dot-like localization centers in InGa _N /Ga _N structures. Materials Research Society Symposia Proceedings, 2004, 831, 534.	0.1	0
568	In-depth and in-plane profiling of light emission properties of InGa _N -based laser diode. Physica Status Solidi A, 2004, 201, 207-211.	1.7	0
569	Study of ZnSe-based green-yellow ridge waveguide laser diodes toward long lifetime operation. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1014-1017.	0.8	0
570	Room-temperature operation of a green monolithic II-VI vertical-cavity surface-emitting laser. AIP Conference Proceedings, 2005, , .	0.4	0
571	Characterization of Stress Relaxation, Dislocations and Crystallographic Tilt Via X-ray Microdiffraction in Ga _N (0001) Layers Grown by Maskless Pendeo-Epitaxy. Materials Research Society Symposia Proceedings, 2005, 875, 1.	0.1	0
572	Polariton Propagation in Shallow-Confinement Heterostructures. , 0, , .		0
573	Diffraction anomalous fine structure investigation of InGa _N quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1662-1666.	0.8	0
574	Spatially Resolved Characterization of Microstructure, Defects and Tilts in Ga _N Layers Grown on Si(111) Substrates by Maskless Cantilever Epitaxy. Materials Research Society Symposia Proceedings, 2006, 934, 1.	0.1	0
575	Spatially Resolved Characterization of Plastic Deformation Induced by Focused-Ion Beam Processing in Structured InGa _N /Ga _N Layers. Materials Research Society Symposia Proceedings, 2007, 1020, 1.	0.1	0
576	Dengue sÃ©vÃ©re avec dÃ©faillance multiviscÃ©rale. JEUR/Journal EuropÃ©en Des Urgences, 2007, 20, 158-160.0.0		0

#	ARTICLE	IF	CITATIONS
577	Homoepitaxial laser diodes emitting at 390 nm and the influence of substrate quality. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 74-77.	0.8	0
578	Light controlled spin properties and radiative coupling of CdSe based quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 3334-3346.	0.8	0
579	Incorporation of QD ensembles in separate confinement heterostructures for long wavelength emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S921-S924.	0.8	0
580	Manipulating the optical properties of CdSe/ZnSSe quantum dot based monolithic pillar microcavities. Journal of Physics: Conference Series, 2010, 210, 012006.	0.4	0
581	Methods to spectrally tune II-VI based monolithic microcavities. Physica Status Solidi (B): Basic Research, 2010, 247, 1539-1542.	1.5	0
582	Temperature dependence of radiative recombination in CdSe quantum dots with enhanced confinement. JETP Letters, 2010, 92, 57-62.	1.4	0
583	Electroluminescence from a Single Self-Assembled CdSe Quantum Dot. , 2010, , .		0
584	Optical Properties of InGaN Quantum Dots in Monolithic Pillar Microcavities. , 2011, , .		0
585	Properties of monolithic InGaN quantum dot pillar microcavities. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1573-1575.	1.8	0
586	Fabrication of ZnSe based microcavities for lasing in the strong coupling regime and polariton confinement. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1267-1272.	0.8	0
587	Nitride Semiconductors. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 897-897.	1.8	0
588	Nitride Semiconductors. Physica Status Solidi (B): Basic Research, 2015, 252, 853-853.	1.5	0
589	Exciton emission from plasmonic-organic-III-V semiconductor nanowires and nanorods. , 2016, , .		0
590	Composition analysis of coaxially grown InGaN multi quantum wells using scanning transmission electron microscopy. Journal of Applied Physics, 2016, 119, 175701.	2.5	0
591	The influence of the quantum confined Stark effect on InGaN/AlGaN quantum dots. Physica Status Solidi (B): Basic Research, 2017, 254, 1600325.	1.5	0
592	Influence of the sample design on the strong light-matter coupling in ZnSe-based periodic structures. Journal of Physics: Conference Series, 2017, 864, 012020.	0.4	0
593	Thermal expansion of GaN at low temperatures - a comparison of bulk and homo- and heteroepitaxial layers. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 391-397.	1.0	0
594	Microwave-Induced Delocalization of Excitons in Ternary Compounds of II-VI and III-V Semiconductors. Acta Physica Polonica A, 2003, 103, 559-566.	0.5	0

#	ARTICLE	IF	CITATIONS
595	Epitaxial technologies for short wavelength optoelectronic devices. , 2004, , 295-317.		0
596	Surface Morphology and Island Shape of MOVPE Grown InGaN Nano-Island Ensembles Studied by STM. Materials Research Society Symposia Proceedings, 2005, 892, 759.	0.1	0
597	Deep Levels Induced by CdTe/ZnTe Quantum Dots. Acta Physica Polonica A, 2011, 119, 630-632.	0.5	0
598	On the Stability of Rare Earth Centers in IIâ€“VI Compounds. Springer Proceedings in Physics, 1989, , 101-104.	0.2	0
599	Optical Characterization of CdZnSe/ZnSe Multiquantum Well System. Acta Physica Polonica A, 1995, 87, 209-212.	0.5	0
600	Statistical Analysis of Local Composition and Luminescence in InGaN Grown by Molecular Beam Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 263-268.	1.0	0
601	Trap and non-trap dispersions in admittance spectra of hexagonal Galliumnitride. , 2017, , 359-362.		0
602	Modulated Ammonia Flow - Low Temperature AlN Buffer LP-MOVPE Growth for High Quality AlGaIn Layers. Acta Physica Polonica A, 2019, 136, 589-592.	0.5	0
603	Electrically Driven Single Quantum Dot Emitter Operating at Room Temperature. Advances in Solid State Physics, 0, , 67-78.	0.8	0
604	Role of Temperature in Arsenic-Induced Antisurfactant Growth of GaN Microrods. ACS Omega, 2022, 7, 24777-24784.	3.5	0